

SCHOTTKY BARRIER DIODE

●Applications

Low current rectification

●Features

Extremelysmall surface mounting type. (SOD923)

Low V_F

High reliability.

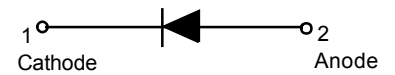
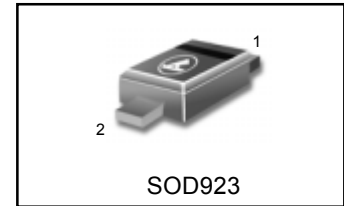
We declare that the material of product compliance with RoHS requirements.

S- Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

●Construction

Silicon epitaxial planar

LRB521CS-30T5G
S-LRB521CS-30T5G



DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
LRB521CS-30T5G S-LRB521CS-30T5G	F	8000/Tape&Reel

●Absolute maximum ratings (Ta=25°C)

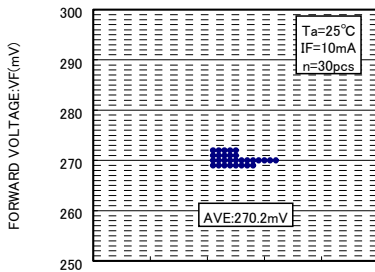
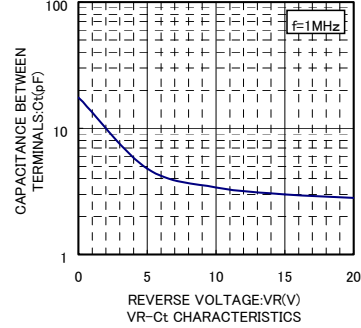
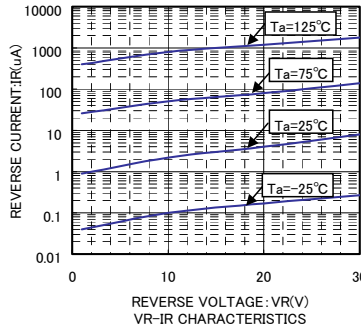
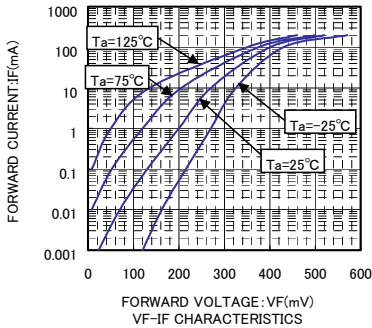
Parameter	Symbol	Limits	Unit
Reverse voltage (DC)	V_R	30	V
Average rectifierd forward current	I_o	100	mA
Forward current surge peak (60Hz·1cyc)	I_{FSM}	500	mA
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	-40 to +125	°C

●Electrical characteristic (Ta=25°C)

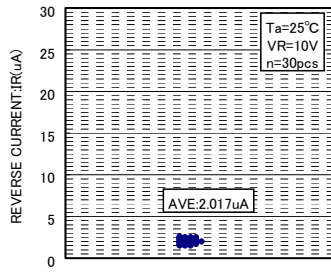
Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward vpltage	V_F	-	-	0.35	V	$I_F=10mA$
Forward vpltage	V_F	-	-	0.4	V	$I_F=20mA$
Reverse current	I_R	-	-	10	μA	$V_R=10V$

LRB521CS-30T5G S-LRB521CS-30T5G

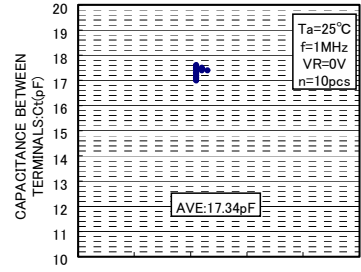
●Electrical characteristic curves



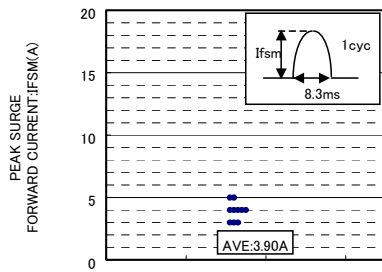
VF DISPERSION MAP



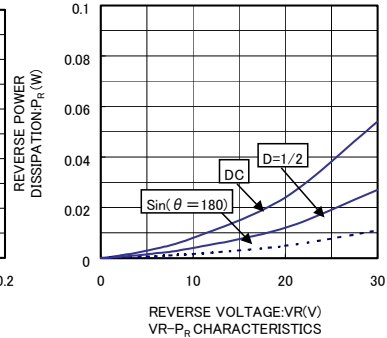
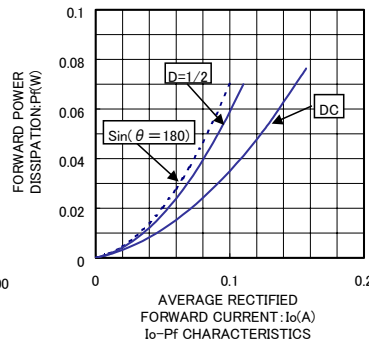
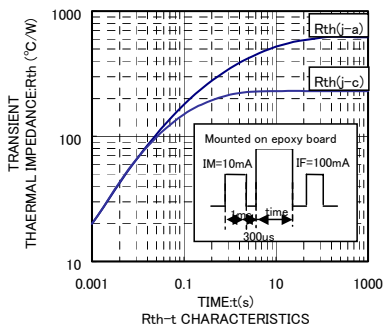
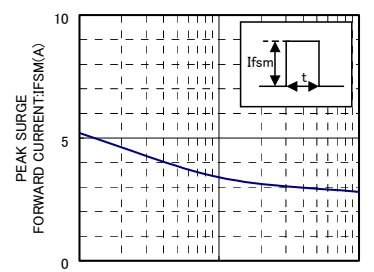
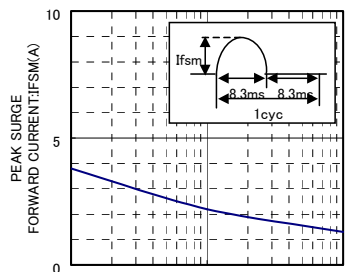
IR DISPERSION MAP

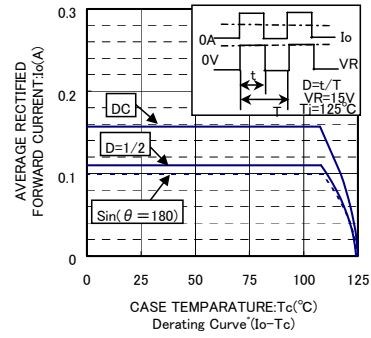
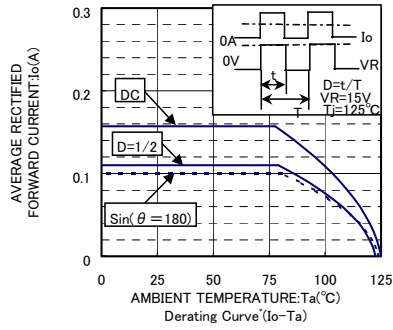


Ct DISPERSION MAP



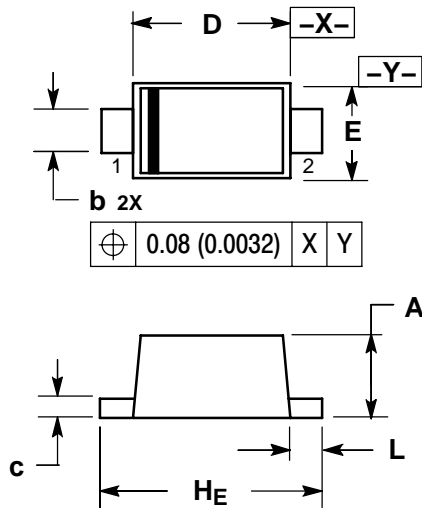
IFSM DISERSION MAP



LRB521CS-30T5G S-LRB521CS-30T5G
Electrical characteristic curves ($T_a=25^{\circ}\text{C}$)


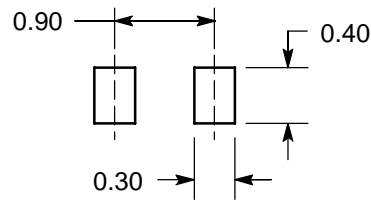
LRB521CS-30T5G S-LRB521CS-30T5G

SOD-923



DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.34	0.39	0.43	0.013	0.015	0.017
b	0.15	0.20	0.25	0.006	0.008	0.010
c	0.07	0.12	0.17	0.003	0.005	0.007
D	0.75	0.80	0.85	0.030	0.031	0.033
E	0.55	0.60	0.65	0.022	0.024	0.026
HE	0.95	1.00	1.05	0.037	0.039	0.041
L	0.05	0.10	0.15	0.002	0.004	0.006

SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS